

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{\text{DS(ON)}}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- ●Ideal for high-frequency switching and synchronous rectification

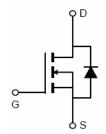
General Features

- V_{DS} =85V, I_D =80A $R_{DS(ON)}$ =7.5m Ω , typical @ V_{GS} =10V
- Excellent gate charge x R_{DS(on)} product(FOM)
- Very low on-resistance R_{DS(on)}
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED! 100% ΔVds TESTED!

TO-220





Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|------------|----------------|-----------|------------|----------|
| NCEP080N85 | NCEP080N85 | TO-220-3L | 1 | 1 | - |

Absolute Maximum Ratings (T_C=25 ℃unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|--|-----------------------|------------|------------|
| Drain-Source Voltage | V _{DS} | 85 | V |
| Gate-Source Voltage | V _G S | ±20 | V |
| Drain Current-Continuous | I _D | 80 | А |
| Drain Current-Continuous(T _C =100°C) | I _D (100℃) | 60 | Α |
| Pulsed Drain Current | I _{DM} | 320 | Α |
| Maximum Power Dissipation | P _D | 100 | W |
| Derating factor | | 0.67 | W/℃ |
| Single pulse avalanche energy (Note 4) | E _{AS} | 352 | mJ |
| Operating Junction and Storage Temperature Range | T_{J}, T_{STG} | -55 To 175 | $^{\circ}$ |

Thermal Characteristic

| Thermal Resistance, Junction-to-Case | $R_{	heta JC}$ | 1.5 | °C/W | |
|--------------------------------------|----------------|-----|------|--|
|--------------------------------------|----------------|-----|------|--|



Electrical Characteristics (T_C=25 [°]C unless otherwise noted)

| Parameter | Symbol | Condition | Min | Тур | Max | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| Off Characteristics | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | V _{GS} =0V I _D =250μA | 85 | | - | V |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} =85V,V _{GS} =0V | - | - | 1 | μA |
| Gate-Body Leakage Current | I _{GSS} | V _{GS} =±20V,V _{DS} =0V | - | - | ±100 | nA |
| On Characteristics (Note 3) | · | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | $V_{DS}=V_{GS}$, $I_{D}=250\mu A$ | 2.0 | 3.0 | 4.0 | V |
| Drain-Source On-State Resistance | R _{DS(ON)} | V _{GS} =10V, I _D =40A | - | 7.5 | 8.0 | mΩ |
| Forward Transconductance | g FS | V _{DS} =5V,I _D =40A | | 50 | - | S |
| Dynamic Characteristics (Note3) | · | | | | | |
| Input Capacitance | C _{lss} | \/ -40\/\/ -0\/ | - | 2059 | - | pF |
| Output Capacitance | C _{oss} | V_{DS} =40V, V_{GS} =0V, F=1.0MHz | - | 393 | - | pF |
| Reverse Transfer Capacitance | C _{rss} | r-1.0ivinz | - | 25.4 | - | pF |
| Switching Characteristics (Note 3) | · | | | | | |
| Turn-on Delay Time | t _{d(on)} | | - | 12 | - | nS |
| Turn-on Rise Time | t _r | V_{DD} =40 V , I_{D} =40 A | - | 9 | - | nS |
| Turn-Off Delay Time | t _{d(off)} | V_{GS} =10 V , R_{G} =1.6 Ω | - | 29 | - | nS |
| Turn-Off Fall Time | t _f | | - | 7 | - | nS |
| Total Gate Charge | Qg | \/ -40\/ -40 \ | - | 41.4 | - | nC |
| Gate-Source Charge | Q _{gs} | V_{DS} =40V, I_{D} =40A, V_{GS} =10V | - | 14.9 | - | nC |
| Gate-Drain Charge | Q _{gd} | V _{GS} -10V | - | 12.5 | - | nC |
| Drain-Source Diode Characteristics | · | | | | | |
| Diode Forward Voltage (Note 2) | V _{SD} | V _{GS} =0V,I _S =40A | - | - | 1.2 | V |
| Diode Forward Current | Is | | - | - | 80 | Α |
| Reverse Recovery Time | t _{rr} | T _J = 25°C, I _F = 40A | - | 55 | - | nS |
| Reverse Recovery Charge | Qrr | $di/dt = 100A/\mu s^{(Note3)}$ | - | 98 | - | nC |

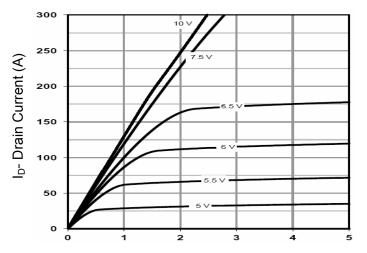
Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Pulse Test: Pulse Width ≤ 300µs, Duty Cycle ≤ 2%.
- 3. Guaranteed by design, not subject to production 4. EAS condition : Tj=25 $^{\circ}\text{C}$,V $_{DD}$ =50V,V $_{G}$ =10V,L=0.25mH,Rg=25 Ω

V1.0

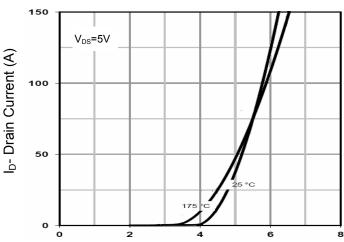


Typical Electrical and Thermal Characteristics



Vds Drain-Source Voltage (V)





Vgs Gate-Source Voltage (V)
Figure 2 Transfer Characteristics

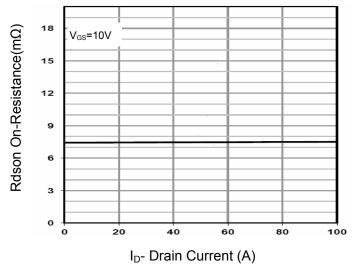


Figure 3 Rdson- Drain Current

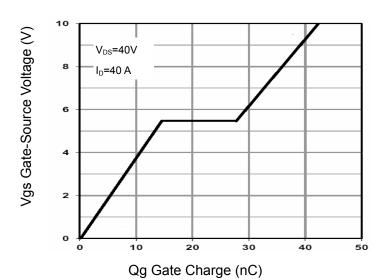


Figure 4 Gate Charge

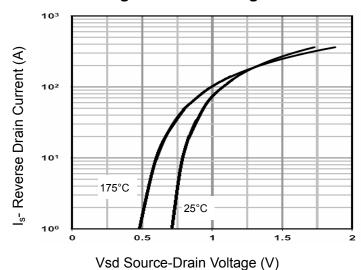


Figure 5 Source- Drain Diode Forward

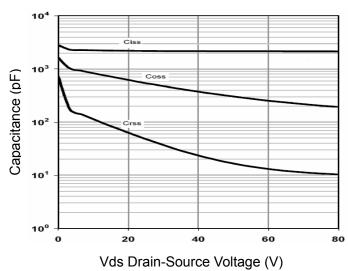
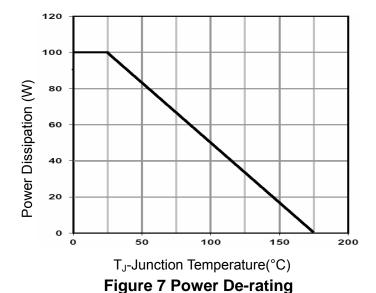
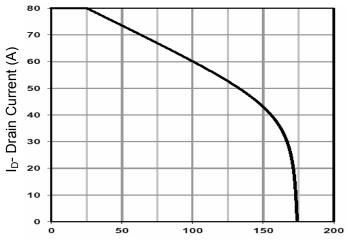


Figure 6 Capacitance vs Vds







T_J-Junction Temperature (°C) **Figure 9 Current De-rating**

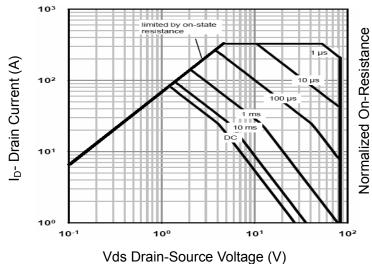


Figure 8 Safe Operation Area

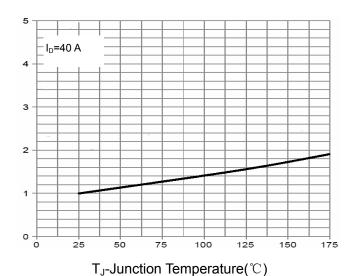
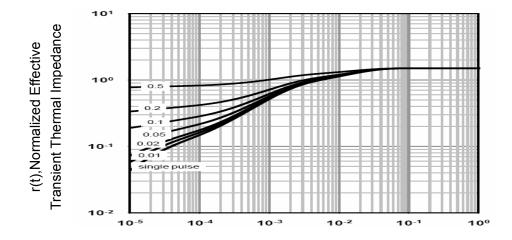


Figure 10 Rdson-Junction Temperature

V1.0

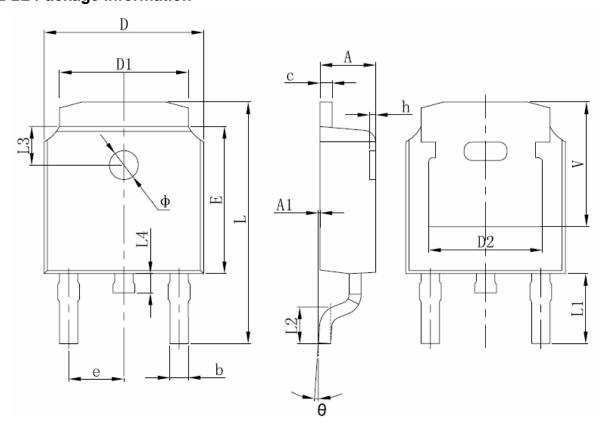


Square Wave Pluse Duration(sec)

Figure 11 Normalized Maximum Transient Thermal Impedance



TO-252-2L Package Information



| Cumbal | Dimensions | In Millimeters | Dimensions In Inches | | |
|--------|------------|----------------|----------------------|-------|--|
| Symbol | Min. | Max. | Min. | Max. | |
| Α | 2.200 | 2.400 | 0.087 | 0.094 | |
| A1 | 0.000 | 0.127 | 0.000 | 0.005 | |
| b | 0.635 | 0.770 | 0.025 | 0.030 | |
| С | 0.460 | 0.580 | 0.018 | 0.023 | |
| D | 6.500 | 6.700 | 0.256 | 0.264 | |
| D1 | 5.100 | 5.460 | 0.201 | 0.215 | |
| D2 | 4.830 | REF. | 0.190 REF. | | |
| E | 6.000 | 6.200 | 0.236 | 0.244 | |
| е | 2.186 | 2.386 | 0.086 | 0.094 | |
| L | 9.712 | 10.312 | 0.382 | 0.406 | |
| L1 | 2.900 | REF. | 0.114 | REF. | |
| L2 | 1.400 | 1.700 | 0.055 | 0.067 | |
| L3 | 1.600 | 0.063 REF. | | REF. | |
| L4 | 0.600 | 1.000 | 0.024 | 0.039 | |
| Ф | 1.100 | 1.300 | 0.043 | 0.051 | |
| θ | 0° | 8° | 0° | 8° | |
| h | 0.000 | 0.300 | 0.000 | 0.012 | |
| V | 5.250 | REF. | 0.207 REF. | | |



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